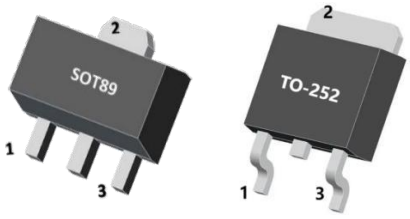
TRANSISTOR (PNP)

Parameter	Value	Unit
V_{CEO}	-30	V
I_C	-3	A

1. BASE
2. COLLECTOR
3. EMITTER



Features

- Complementary to NPN Transistor D882
- High current output up to 3A
- Low saturation voltage

Applications

- Audio power amplifier
- DC-DC converter
- Voltage regulator

Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage		-40	V
V_{CEO}	Collector-Emitter Voltage		-30	V
V_{EBO}	Emitter-Base Voltage	TO-252	-7	V
		SOT-89	-5	
I_C	Collector Current (DC)		-3	A
I_{CP}	Collector Current (Pulse)		-7	A
I_B	Base Current		-0.6	A
P_C	Collector Dissipation	TO-252	1	W
		SOT-89	0.5	
T_J	Operating Junction Temperature		+150	℃
T_{STG}	Storage Temperature		-55 to +150	℃

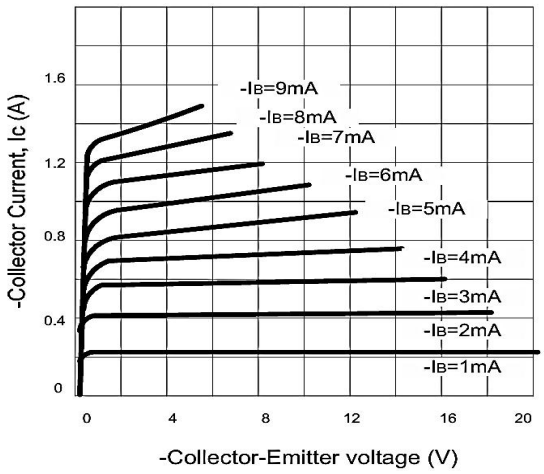
Note:
Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Electrical Characteristics(Ta=25℃ unless otherwise noted)

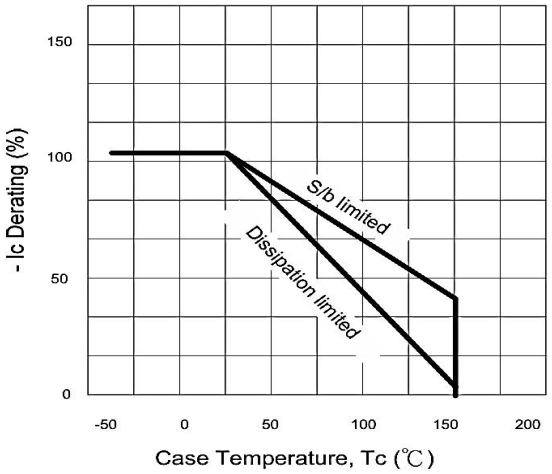
Parameter	Symbol		Test Conditions		Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V_{CBO}		I_C=-100μA, I_E=0		-40			V
Collector-Emitter Breakdown Voltage	V_{CEO}		I_C=-1mA, I_B=0		-30			V
Emitter-Base Breakdown Voltage	V_{EBO}		I_E=-100μA, I_C=0	TO-252	-7			V
				SOT-89	-5			
Collector Cut-Off Current	I_{CBO}		V_{CB}=-30V ,I_E=0				-1	μA
Collector Cut-Off Current	I_{CEO}		V_{CE}=-30V ,I_B=0				-1	μA
Emitter Cut-Off Current	I_{EBO}		V_{EB}=-5V, I_C=0				-1	μA
DC Current Gain (Note) (CLASSIFICATION OF hFE2)	h_{FE1}		V_{CE}=-2V, I_C=-20mA		30	200		
	hFE2	A	V_{CE}=-2V, I_C=-1A		100		200	
		B			160		320	
		C			200		400	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		I_C=-2A, I_B=-0.2A			-0.3	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$		I_C=-2A, I_B=-0.2A			-1.0	-2.0	V
Current Gain Bandwidth Product	f_T		V_{CE}=-5V, I_C=-0.1A			80		MHz
Output Capacitance	C_{OB}		V_{CB}=-10V, I_E=0, f=1MHz			45		pF

Typical Characteristics

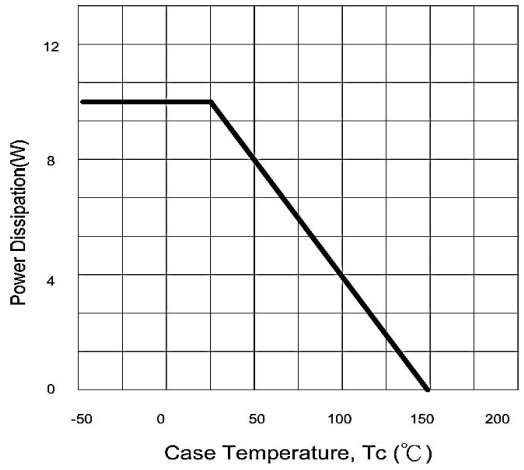
Static Characteristics



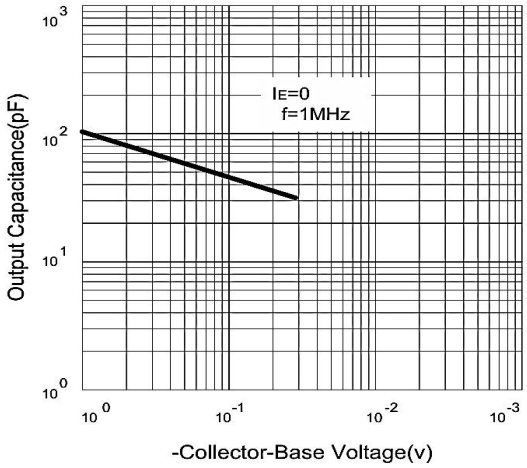
Derating Curve of Safe Operating Areas



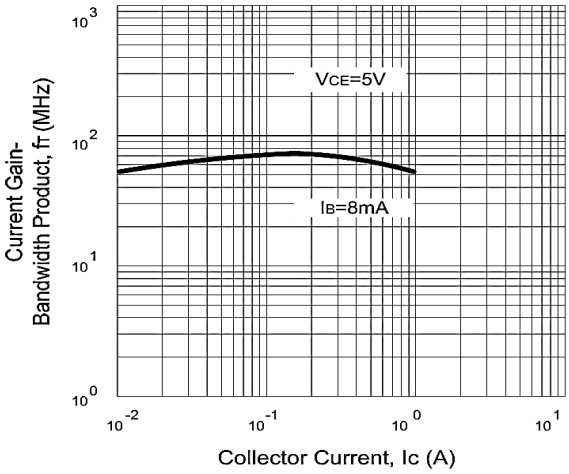
Power Derating



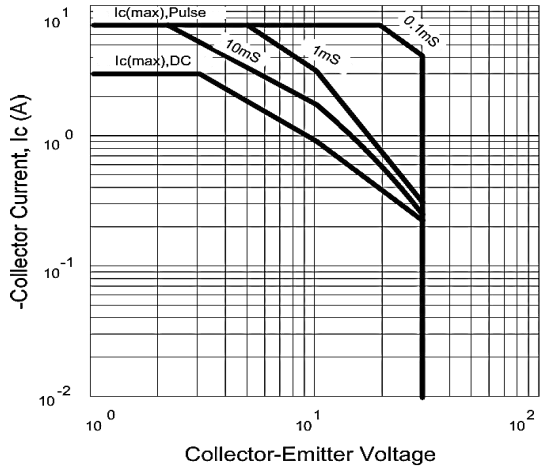
Collector Output Capacitance



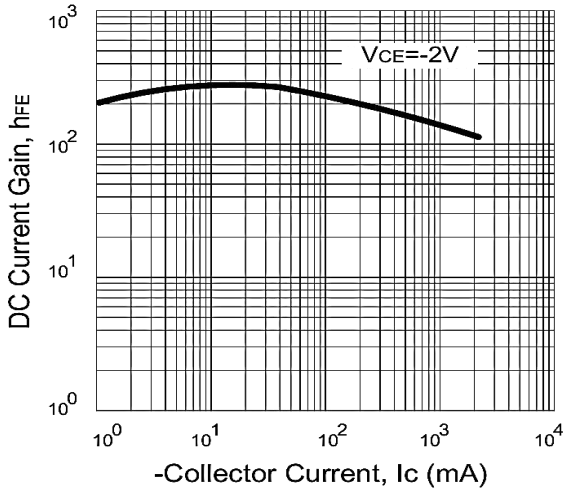
Current Gain-
Bandwidth Product



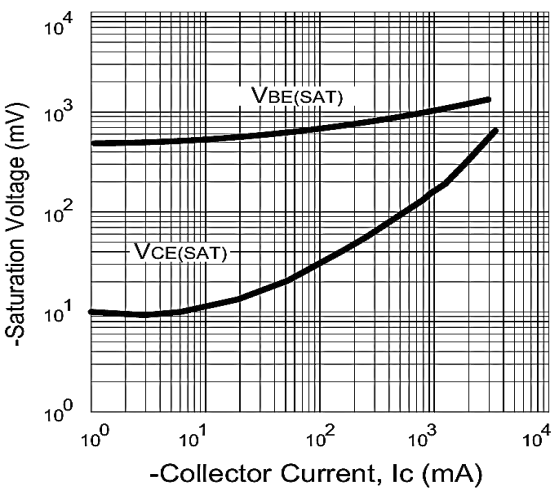
Safe Operating Area



DC Current Gain

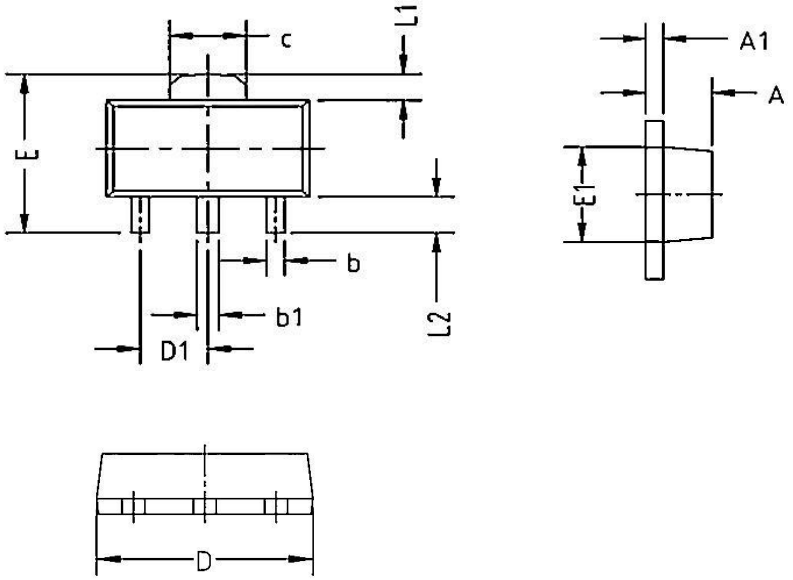


Saturation Voltage



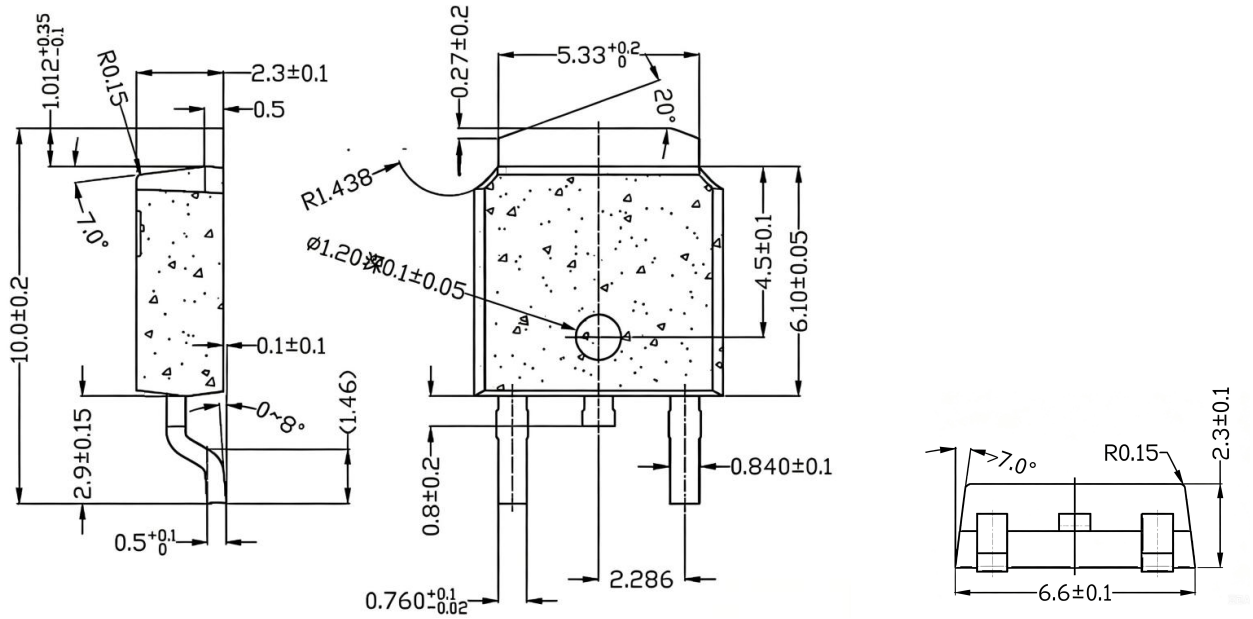
Package Outline Dimensions

SOT-89



COMMON DIMENSION(MM)			
PKG	SOT-89		
Symbol	MIN	MON	MAX
A	1.450	1.500	1.550
A1	0.350	0.400	0.450
b	0.350	0.400	0.48
b1	0.430	0.480	0.550
C	1.500	1.550	1.650
D	4.450	4.550	4.700
D1	1.470	1.500	1.550
E	4.100	4.200	4.300
E1	2.500	2.550	2.650
L1	0.650	0.700	0.750
L2	0.900	0.950	1.000

TO-252



***Important Usage Information and Disclaimer**

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